

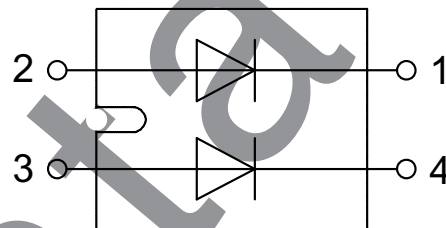
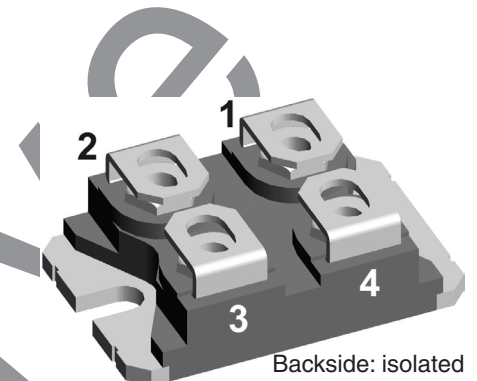
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SiC Schottky Diode

$$\begin{aligned} V_{RRM} &= 1200 \text{ V} \\ I_{FAV} &= 2 \times 43 \text{ A} \end{aligned}$$

Ultra fast switching
Zero reverse recovery

Part number
DCG85X1200NA



Features / Advantages:

- Ultra fast switching
- Zero reverse recovery
- Zero forward recovery
- Temperature independent switching behavior
- Positive temperature coefficient of forward voltage
- $T_{vj} = 175^{\circ}\text{C}$

Applications:

- Solar inverter
- Uninterruptible power supply (UPS)
- Welding equipment
- Switched-mode power supplies
- Medical equipment
- High speed rectifier

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate with Aluminium nitride isolation for low thermal resistance
- Advanced power cycling

Terms & Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;
- the conclusion of quality agreements;
- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

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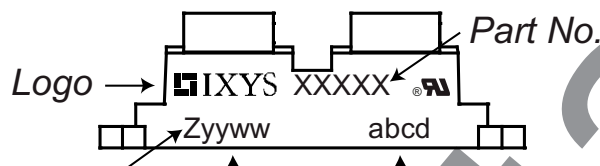
SiC Diode				Ratings			
Symbol	Definitions	Conditions		min.	typ.	max.	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 175^{\circ}\text{C}$		70 130	400 800	μA μA
V_F	forward voltage	$I_F = 20\text{ A}$ $I_F = 40\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$		1.5	1.8	V V
			$T_{VJ} = 175^{\circ}\text{C}$		2.20	3.0	V V
		$T_C = 80^{\circ}\text{C}$ $T_C = 100^{\circ}\text{C}$	rectangular, $d = 0.5$ $T_{VJ} = 175^{\circ}\text{C}$			43 38	A A
I_{F25}	forward current		$T_C = 25^{\circ}\text{C}$			76	A
I_{F80}			$T_C = 80^{\circ}\text{C}$			59	A
I_{F100}			$T_C = 100^{\circ}\text{C}$			52	A
I_{FSM}	max forward surge current	$t = 10\text{ ms, half sine (50 Hz)}$ $t_p = 10\text{ }\mu\text{s, pulse}$	$T_{VJ} = 25^{\circ}\text{C}$ $V_R = 0\text{ V}$			200 1150	A A
Q_C	total capacitive charge	$V_R = 800\text{ V, } I_F = 40\text{ A}$ $di/dt = 400\text{ A}/\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$		260		nC
C	total capacitance	$V_R = 0\text{ V}$ $V_R = 400\text{ V}$ $V_R = 800\text{ V}$	$T_{VJ} = 25^{\circ}\text{C, } f = 1\text{ MHz}$		3000		pF
					185		pF
					135		pF
R_{thJC}	thermal resistance junction to case	with heatsink compound; IXYS test setup				0.57	K/W
R_{thJH}	thermal resistance junction to heatsink				0.72		K/W

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Package Outlines SOT-227B (minibloc)				Ratings		
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			100	A
T_{stg}	storage temperature		-40		150	°C
T_{op}	operation temperature		-40		150	°C
T_{VJ}	virtual junction temperature		-40		175	°C
Weight				30		g
M_D	mounting torque ¹⁾	screws to heatsink terminal connection screws			1.5 1.3	Nm Nm
d_{Spp}	creepage distance on surface	terminal to terminal	10.5			mm
d_{Spb}		terminal to backside	8.5			mm
d_{App}	striking distance through air	terminal to terminal	3.2			mm
d_{Apb}		terminal to backside	6.8			mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute	3000 2500			V V
C_P	coupling capacity per switch	between shorted terminals of diodes and back side metalization				pF

¹⁾ further information see application note IXAN0073 on www.ixys.com/TechnicalSupport/appnotes.aspx (General / Isolation, Mounting, Soldering, Cooling)

Product Marking



Part description

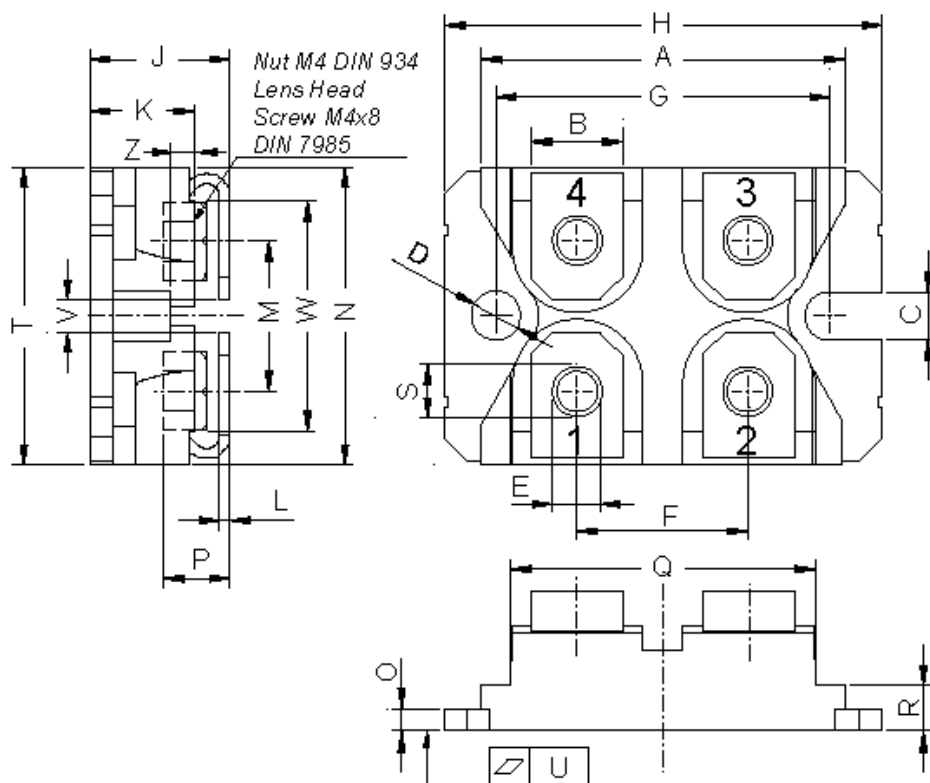
D = Diode
C = SiC
G = extreme fast
85 = Current Rating [A]
X = Parallel legs
1200 = Reverse Voltage [V]
NA = SOT-227 (minibloc)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	DCG85X1200NA	DCG85X1200NA	Tube	10	520214

Equivalent Circuits for Simulation ^{*} on die level

		$T_{VJ} = 125^{\circ}\text{C}$	$T_{VJ} = 175^{\circ}\text{C}$
$V_{0\max}$	threshold voltage	0.73	V
$R_{0\max}$	slope resistance [*]	35.2	mΩ

Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106

